# **Complementary Power Transistors**

## **DPAK For Surface Mount Applications**

... for general purpose power and switching such as output or driver stages in applications such as switching regulators, converters, and power amplifiers.

- Lead Formed for Surface Mount Application in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves ("-1" Suffix)
- Lead Formed Version in 16 mm Tape and Reel for Surface Mount ("T4" Suffix)
- Electrically Similar to Popular D44H/D45H Series
- Low Collector Emitter Saturation Voltage VCE(sat) = 1.0 Volt Max @ 8.0 Amperes
- Fast Switching Speeds
- · Complementary Pairs Simplifies Designs

#### **MAXIMUM RATINGS**

Rating	Symbol	D44H11 or D45H11	Unit
Collector–Emitter Voltage	VCEO	80	Vdc
Emitter-Base Voltage	V <sub>EB</sub>	5	Vdc
Collector Current — Continuous Peak	IC	8 16	Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	20 0.16	Watts W/°C
Total Power Dissipation (1)  @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	1.75 0.014	Watts W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C

#### THERMAL CHARACTERISTICS

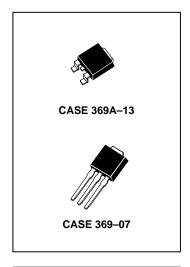
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	6.25	°C/W
Thermal Resistance, Junction to Ambient (1)	$R_{\theta JA}$	71.4	°C/W
Lead Temperature for Soldering	TL	260	°C

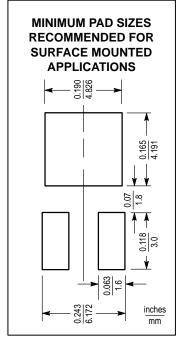
(1) These ratings are applicable when surface mounted on the minimum pad size recommended.

## NPN MJD44H11\* PNP MJD45H11\*

\*Motorola Preferred Device

SILICON
POWER TRANSISTORS
8 AMPERES
80 VOLTS
20 WATTS





Preferred devices are Motorola recommended choices for future use and best overall value.



### MJD44H11 MJD45H11

## **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						•
Collector–Emitter Sustaining Voltage (I <sub>C</sub> = 30 mA, I <sub>B</sub> = 0)		VCEO(sus)	80	_	_	Vdc
Collector Cutoff Current (VCE = Rated VCEO, VBE = 0)		ICES	_	_	10	μА
Emitter Cutoff Current (VEB = 5 Vdc)		I <sub>EBO</sub>	_	_	50	μА
ON CHARACTERISTICS				•		•
Collector–Emitter Saturation Voltage (IC = 8 Adc, IB = 0.4 Adc)		VCE(sat)	_	_	1	Vdc
Base–Emitter Saturation Voltage (IC = 8 Adc, IB = 0.8 Adc)		VBE(sat)	_	_	1.5	Vdc
DC Current Gain (V <sub>CE</sub> = 1 Vdc, I <sub>C</sub> = 2 Adc)		hFE	60	_	_	_
DC Current Gain (V <sub>CE</sub> = 1 Vdc, I <sub>C</sub> = 4 Adc)			40	_	_	
DYNAMIC CHARACTERISTICS		•				
Collector Capacitance (V <sub>CB</sub> = 10 Vdc, f <sub>test</sub> = 1 MHz)	MJD44H11 MJD45H11	C <sub>cb</sub>		130 230	_	pF
Gain Bandwidth Product (I <sub>C</sub> = 0.5 Adc, V <sub>CE</sub> = 10 Vdc, f = 20 MHz)	MJD44H11 MJD45H11	fΤ	_ _ _	50 40	_ _	MHz
SWITCHING TIMES						
Delay and Rise Times (I <sub>C</sub> = 5 Adc, I <sub>B1</sub> = 0.5 Adc)	MJD44H11 MJD45H11	t <sub>d</sub> + t <sub>r</sub>		300 135	_ _	ns
Storage Time (I <sub>C</sub> = 5 Adc, I <sub>B1</sub> = I <sub>B2</sub> = 0.5 Adc)	MJD44H11 MJD45H11	t <sub>S</sub>		500 500	_	ns
Fall Time (I <sub>C</sub> = 5 Adc, I <sub>B1</sub> = I <sub>B2</sub> = 0.5 Adc)	MJD44H11 MJD45H11	tf		140 100	_ _	ns

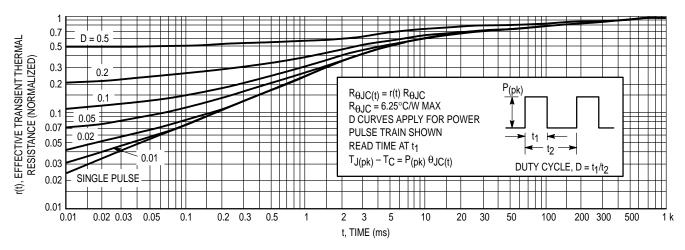


Figure 1. Thermal Response

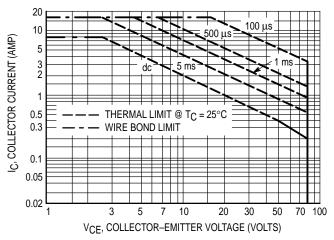


Figure 2. Maximum Forward Bias Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 2 is based on  $T_{J(pk)} = 150^{\circ}C$ ;  $T_{C}$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \le 150^{\circ}C$ .  $T_{J(pk)}$  may be calculated from the data in Figure 1. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

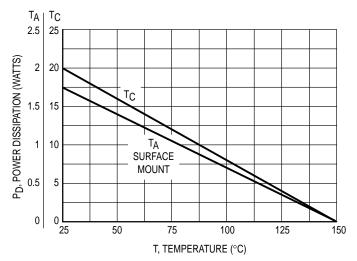


Figure 3. Power Derating

#### **MJD44H11 MJD45H11**

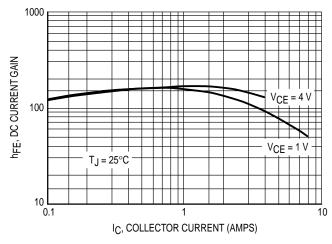


Figure 4. MJD44H11 DC Current Gain

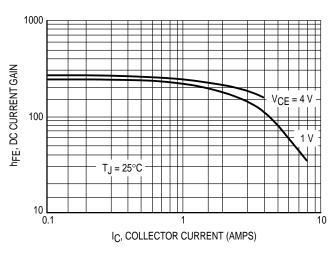


Figure 5. MJD45H11 DC Current Gain

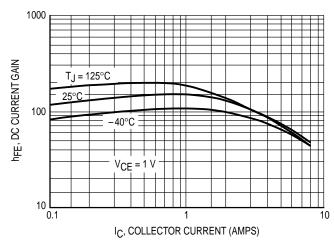


Figure 6. MJD44H11 Current Gain versus Temperature

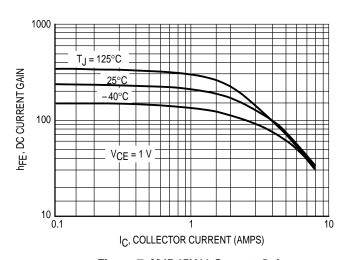


Figure 7. MJD45H11 Current Gain versus Temperature

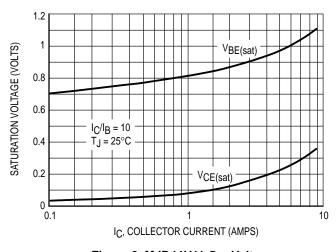


Figure 8. MJD44H11 On-Voltages

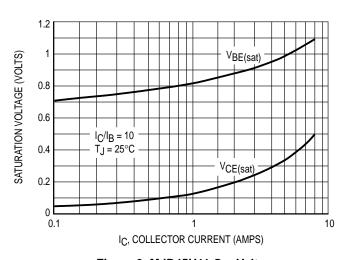
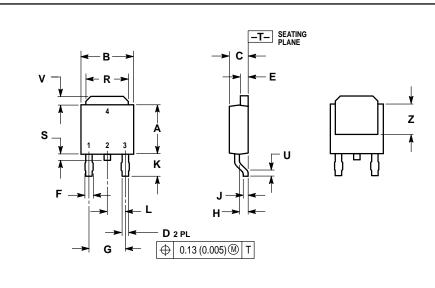


Figure 9. MJD45H11 On-Voltages

#### **PACKAGE DIMENSIONS**

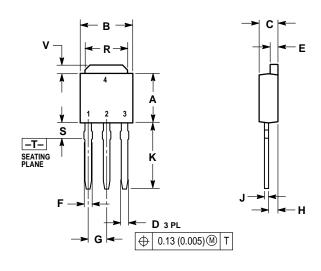


- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.250	5.97	6.35
В	0.250	0.265	6.35	6.73
С	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
Е	0.033	0.040	0.84	1.01
F	0.037	0.047	0.94	1.19
G	0.180 BSC		4.58 BSC	
Н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.102	0.114	2.60	2.89
L	0.090	0.090 BSC		BSC
R	0.175	0.215	4.45	5.46
S	0.020	0.050	0.51	1.27
U	0.020		0.51	
٧	0.030	0.050	0.77	1.27
Z	0.138		3.51	

- STYLE 1:
  PIN 1. BASE
  2. COLLECTOR
  3. EMITTER
  4. COLLECTOR

#### **CASE 369A-13 ISSUE W**



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
   CONTROLLING DIMENSION: INCH.

	INC	HES	MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.250	5.97	6.35
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G	0.090 BSC		2.29 BSC	
Н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.175	0.215	4.45	5.46
S	0.050	0.090	1.27	2.28
٧	0.030	0.050	0.77	1.27

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

**CASE 369-07 ISSUE K** 

#### **MJD44H11 MJD45H11**

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